



Features

- Low profile package
- Ideal for automated placement
- Glass passivated chip junction
- Fast switching for high efficiency
- High forward surge capability
- High temperature soldering:
260°C/10 seconds at terminals
- Component in accordance to
RoHS 2002/95/1 and WEEE 2002/96/EC



Mechanical Data

- **Case:** JEDEC MSMA molded plastic body over glass passivated chip
- **Terminals:** Solder plated, solderable per J-STD-002B and JESD22-B102D
- **Polarity:** Laser band denotes cathode end

Major Ratings and Characteristics

$I_{F(AV)}$	1.0 A
V_{RRM}	50 V to 1000 V
I_{FSM}	30 A
t_{rr}	150nS, 250nS, 500nS
V_F	1.3 V
$T_j \text{ max.}$	150 °C

Maximum Ratings & Thermal Characteristics

($T_A = 25\text{ °C}$ unless otherwise noted)

Items	Symbol	MAFR 1A	MAFR 1B	MAFR 1D	MAFR 1G	MAFR 1J	MAFR 1K	MAFR 1M	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum average forward rectified current	$I_{F(AV)}$	1.0							A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load	I_{FSM}	30							A
Thermal resistance from junction to lead ⁽¹⁾	$R_{\theta JL}$	35							°C/W
Operating junction and storage temperature range	T_J, T_{STG}	-55 to +150							°C

Note 1: Mounted on P.C.B. with 0.2 x 0.2" (5.0 x 5.0mm) copper pad areas.

Electrical Characteristics ($T_A = 25\text{ °C}$ unless otherwise noted)

Items	Test conditions	Symbol	MAFR1A~MAFR1G	MAFR1J	MAFR1K~MAFR1M	UNIT
Instantaneous forward voltage	$I_F = 1.0A^{(2)}$	V_F	1.3			V
Reverse current	$V_R = V_{DC}$ $T_J = 25\text{ °C}$ $T_J = 125\text{ °C}$	I_R	5 100			μA
Reverse recovery time	$I_F = 0.5\text{ A}, I_R = 1.0\text{ A}, I_{rr} = 0.25\text{ A}$	t_{rr}	150	250	500	nS
Typical junction capacitance	4.0V, 1.0MHz	C_J	15		10	pF

Note 2: Pulse test: 300μs pulse width, 1% duty cycle.



MAFR1A~MAFR1M

Surface Mount Fast Recovery Rectifiers

Characteristic Curves ($T_A=25^\circ\text{C}$ unless otherwise noted)

Fig.1 Forward Current Derating Curve

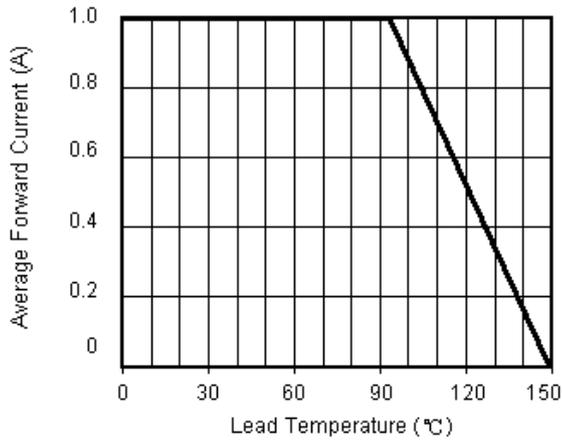


Fig.2 Maximum Non-Repetitive Peak Forward Surge Current

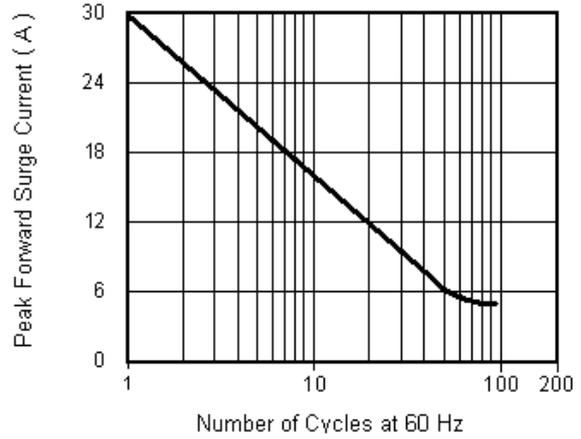


Fig.3 Typical Instantaneous Forward Characteristics

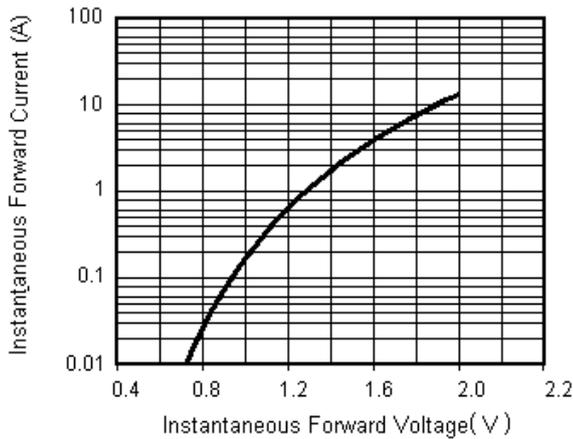


Fig.4 Typical Reverse Leakage Characteristics

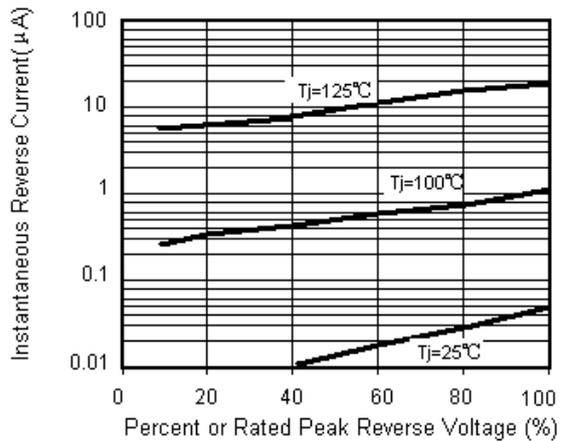


Fig.5 Typical Junction Capacitance

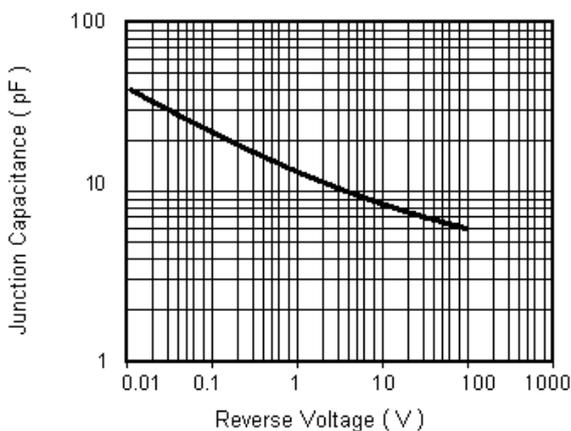
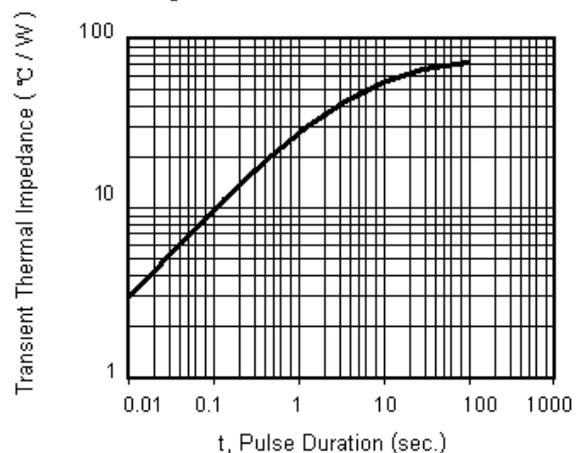
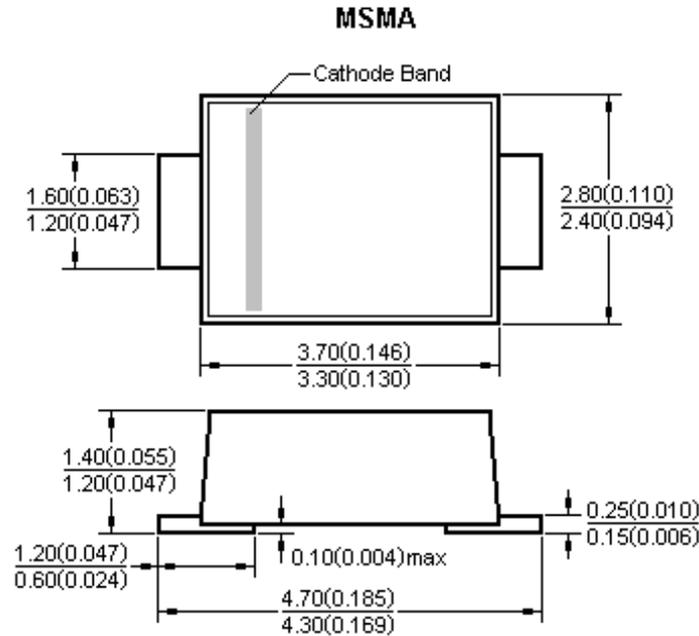


Fig.6 Transient Thermal Impedance





Package Outline



Dimensions in millimeters and (inches)

Notice

- Product is intended for use in general electronics applications.
- Product should be worked less than the ratings; if exceeded, may cause permanent damage or introduce latent failure mechanisms.
- The absolute maximum ratings are rated values and must not be exceeded during operation. The following are the general derating methods you design a circuit with a device.
 - $I_{F(AV)}$: We recommend that the worst case current be no greater than 80% .
 - I_{FSM} : This rating specifies the non-repetitive peak current. This is only applied for an abnormal operation, which the general during the lifespan of the device.
 - T_J : Derate this rating when using a device in order to ensure high reliability. We recommend that the device be used at a T_J of below 125°C.

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